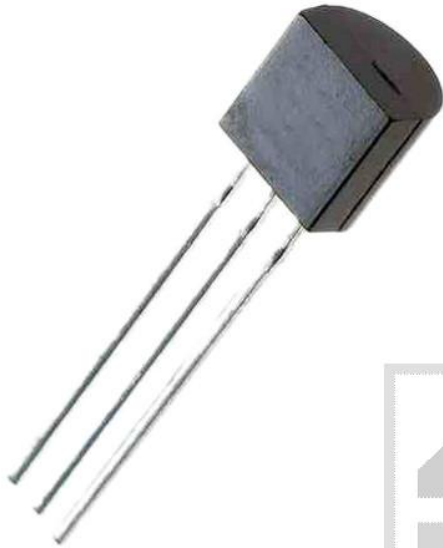




# SS8050CBU;FSC;TO92;tranzystor; NPN;1.5A;40V;1W



## Dane techniczne:

Nazwa: SS8050CBU  
Typ tranzystora: bipolarny  
Kierunek przewodnictwa: NPN  
Prąd kolektora: 1.5A  
Napięcie kolektor-emiter: 40V  
Moc: 1W  
Montaż: przewlekany(THT)  
Obudowa: TO92  
Producent: FSC

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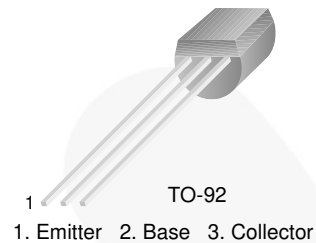
November 2014

# SS8050

## NPN Epitaxial Silicon Transistor

### Features

- 2 W Output Amplifier of Portable Radios in Class B Push-pull Operation.
- Complimentary to SS8550
- Collector Current:  $I_C = 1.5 \text{ A}$



### Ordering Information

| Part Number | Top Mark | Package  | Packing Method |
|-------------|----------|----------|----------------|
| SS8050BBU   | S8050    | TO-92 3L | Bulk           |
| SS8050CBU   | S8050    | TO-92 3L | Bulk           |
| SS8050CTA   | S8050    | TO-92 3L | Ammo           |
| SS8050DBU   | S8050    | TO-92 3L | Bulk           |
| SS8050DTA   | S8050    | TO-92 3L | Ammo           |

### Absolute Maximum Ratings

Stresses exceeding the absolute maximum ratings may damage the device. The device may not function or be operable above the recommended operating conditions and stressing the parts to these levels is not recommended. In addition, extended exposure to stresses above the recommended operating conditions may affect device reliability. The absolute maximum ratings are stress ratings only. Values are at  $T_A = 25^\circ\text{C}$  unless otherwise noted.

| Symbol    | Parameter                 | Value      | Unit             |
|-----------|---------------------------|------------|------------------|
| $V_{CBO}$ | Collector-Base Voltage    | 40         | V                |
| $V_{CEO}$ | Collector-Emitter Voltage | 25         | V                |
| $V_{EBO}$ | Emitter-Base Voltage      | 6          | V                |
| $I_C$     | Collector Current         | 1.5        | A                |
| $T_J$     | Junction Temperature      | 150        | $^\circ\text{C}$ |
| $T_{STG}$ | Storage Temperature       | -65 to 150 | $^\circ\text{C}$ |

**Thermal Characteristics<sup>(1)</sup>**

Values are at  $T_A = 25^\circ\text{C}$  unless otherwise noted.

| Symbol          | Parameter                               | Value | Unit                      |
|-----------------|---|-------|---------------------------|
| $P_D$           | Power Dissipation                       | 1     | W                         |
|                 | Derate Above $25^\circ\text{C}$         | 8     | mW/ $^\circ\text{C}$      |
| $R_{\theta JA}$ | Thermal Resistance, Junction-to-Ambient | 125   | $^\circ\text{C}/\text{W}$ |

**Note:**

1. PCB size: FR-4, 76 mm x 114 mm x 1.57 mm (3.0 inch x 4.5 inch x 0.062 inch) with minimum land pattern size.

**Electrical Characteristics**

Values are at  $T_A = 25^\circ\text{C}$  unless otherwise noted.

| Symbol        | Parameter                            | Conditions   | Min. | Typ. | Max. | Unit |
|---------------|--------------------------------------|--|------|------|------|------|
| $BV_{CBO}$    | Collector-Base Breakdown Voltage     | $I_C = 100 \mu\text{A}$ , $I_E = 0$                          | 40   |      |      | V    |
| $BV_{CEO}$    | Collector-Emitter Breakdown Voltage  | $I_C = 2 \text{ mA}$ , $I_B = 0$                             | 25   |      |      | V    |
| $BV_{EBO}$    | Emitter-Base Breakdown Voltage       | $I_E = 100 \mu\text{A}$ , $I_C = 0$                          | 6    |      |      | V    |
| $I_{CBO}$     | Collector Cut-Off Current            | $V_{CB} = 35 \text{ V}$ , $I_E = 0$                          |      |      | 100  | nA   |
| $I_{EBO}$     | Emitter Cut-Off Current              | $V_{EB} = 6 \text{ V}$ , $I_C = 0$                           |      |      | 100  | nA   |
| $h_{FE1}$     | DC Current Gain                      | $V_{CE} = 1 \text{ V}$ , $I_C = 5 \text{ mA}$                | 45   |      |      |      |
| $h_{FE2}$     |                                      | $V_{CE} = 1 \text{ V}$ , $I_C = 100 \text{ mA}$              | 85   |      | 300  |      |
| $h_{FE3}$     |                                      | $V_{CE} = 1 \text{ V}$ , $I_C = 800 \text{ mA}$              | 40   |      |      |      |
| $V_{CE(sat)}$ | Collector-Emitter Saturation Voltage | $I_C = 800 \text{ mA}$ , $I_B = 80 \text{ mA}$               |      |      | 0.5  | V    |
| $V_{BE(sat)}$ | Base-Emitter Saturation Voltage      | $I_C = 800 \text{ mA}$ , $I_B = 80 \text{ mA}$               |      |      | 1.2  | V    |
| $V_{BE(on)}$  | Base-Emitter On Voltage              | $V_{CE} = 1 \text{ V}$ , $I_C = 10 \text{ mA}$               |      |      | 1    | V    |
| $C_{ob}$      | Output Capacitance                   | $V_{CB} = 10 \text{ V}$ , $I_E = 0$ ,<br>$f = 1 \text{ MHz}$ |      | 9.0  |      | pF   |
| $f_T$         | Current Gain Bandwidth Product       | $V_{CE} = 10 \text{ V}$ , $I_C = 50 \text{ mA}$              | 100  |      |      | MHz  |

 **$h_{FE}$  Classification**

| Classification | B        | C         | D         |
|----------------|----------|-----------|-----------|
| $h_{FE2}$      | 85 ~ 160 | 120 ~ 200 | 160 ~ 300 |

## Typical Performance Characteristics

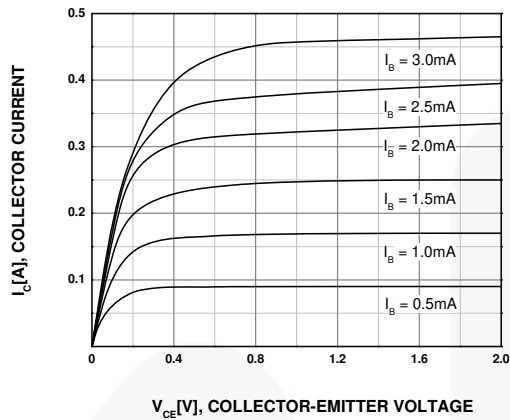


Figure 1. Static Characteristic

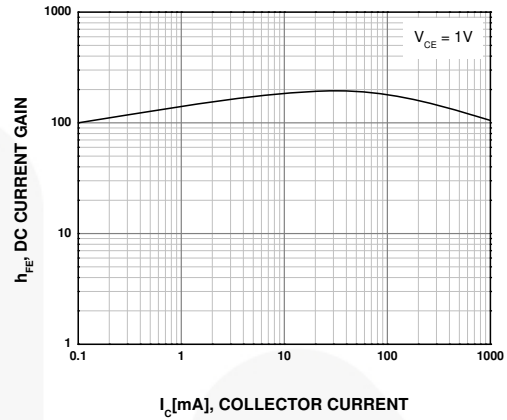


Figure 2. DC Current Gain

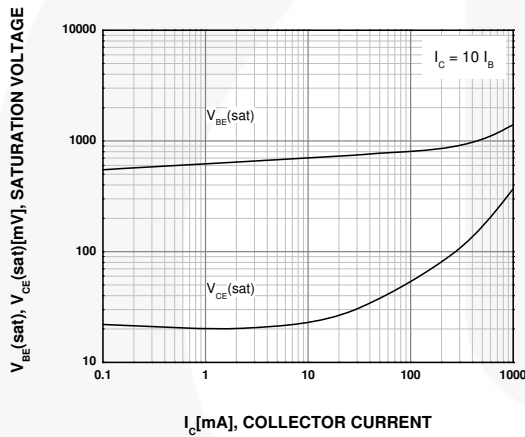


Figure 3. Base-Emitter Saturation Voltage and Collector-Emitter Saturation Voltage

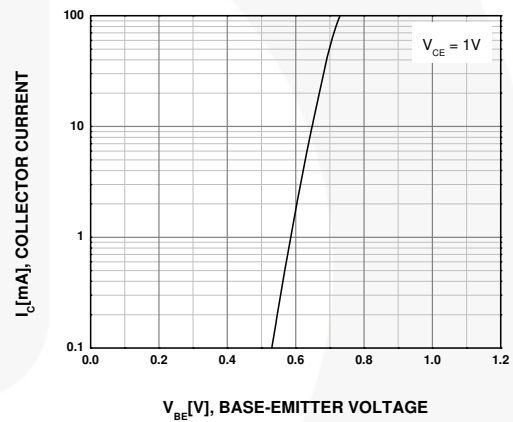


Figure 4. Base-Emitter On Voltage

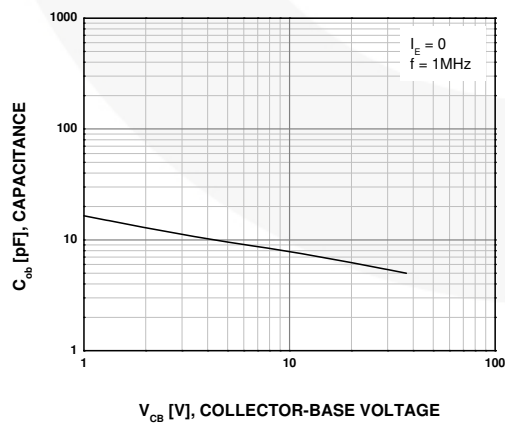


Figure 5. Collector Output Capacitance

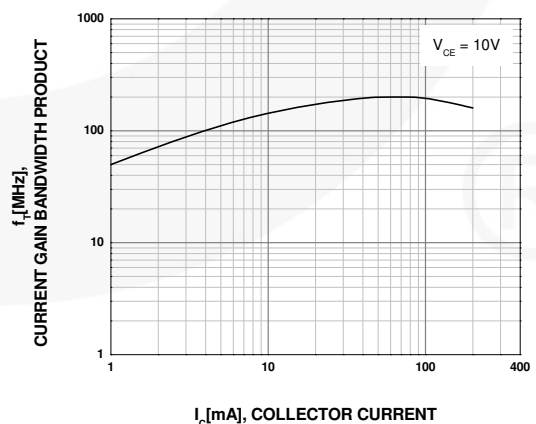
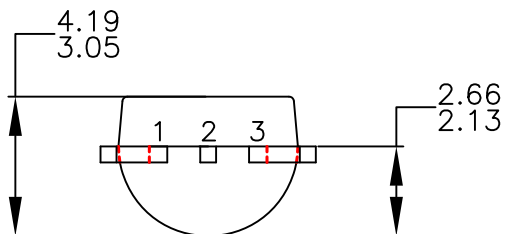
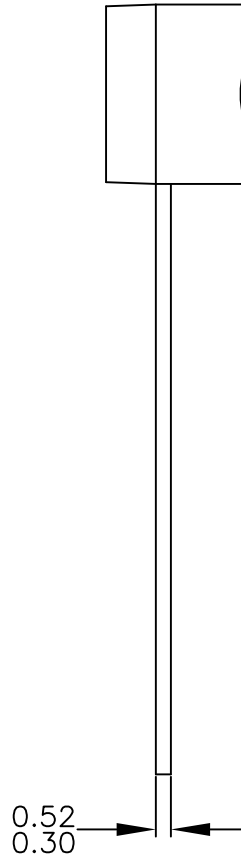
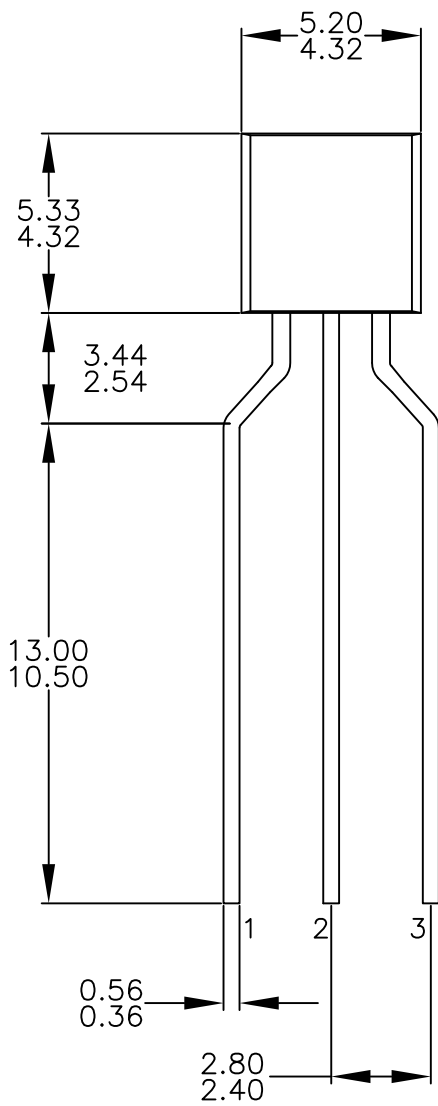
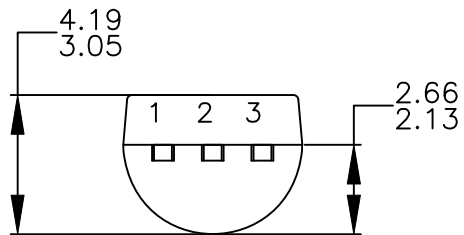
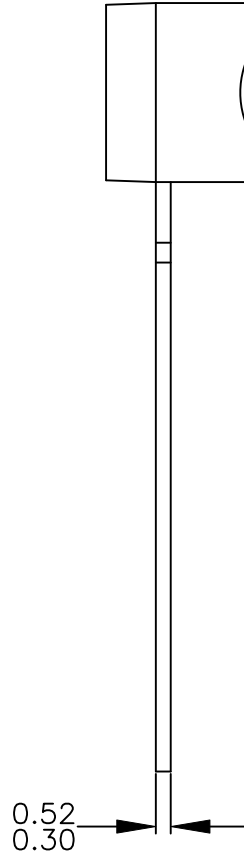
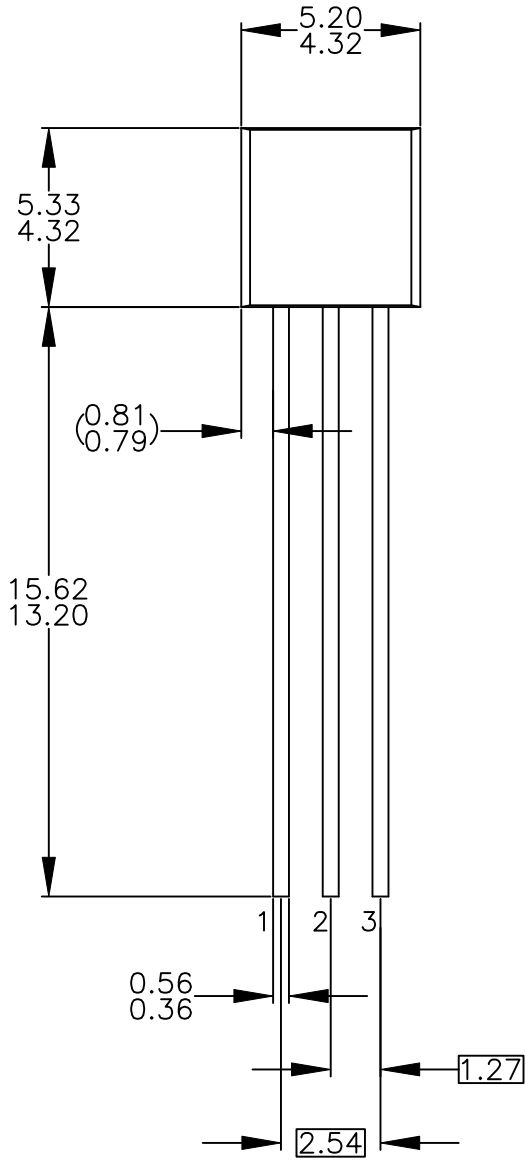


Figure 6. Current Gain Bandwidth Product



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- B. ALL DIMENSIONS ARE IN MILLIMETERS.
- C. DRAWING CONFORMS TO ASME Y14.5M-2009.
- D. DRAWING FILENAME: MKT-ZA03FREV3.
- E. FAIRCHILD SEMICONDUCTOR.



NOTES: UNLESS OTHERWISE SPECIFIED






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- B) ALL DIMENSIONS ARE IN MILLIMETERS.
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